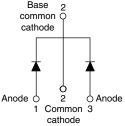
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VS-10CTQ150PbF, VS-10CTQ150-N3

**Vishay Semiconductors** 

# Schottky Rectifier, 2 x 5 A Base





PRODUCT SUMMARY						
Package	TO-220AB					
I <sub>F(AV)</sub>	2 x 5 A					
V <sub>R</sub>	150 V					
V <sub>F</sub> at I <sub>F</sub>	0.73 V					
I <sub>RM</sub> max.	7 mA at 125 °C					
T <sub>J</sub> max.	175 °C					
Diode variation	Common cathode					
E <sub>AS</sub>	6.75 mJ					

### **FEATURES**

- 175 °C T<sub>J</sub> operation
- · Center tap configuration
- Low forward voltage drop
- High frequency operation
- epoxy RoHS • High purity, high temperature COMPLIANT encapsulation for enhanced mechanical strength HALOGEN and moisture resistance FREE



- · Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

### DESCRIPTION

This center tap Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL CHARACTERISTICS VALUES UNITS								
I <sub>F(AV)</sub>	Rectangular waveform	10	А					
V <sub>RRM</sub>		150	V					
I <sub>FSM</sub>	t <sub>p</sub> = 5 μs sine	620	А					
V <sub>F</sub>	5 A <sub>pk</sub> , T <sub>J</sub> = 125 °C (per leg)	0.73	V					
TJ	Range	- 55 to 175	°C					

VOLTAGE RATINGS							
PARAMETER	SYMBOL	VS-10CTQ150PbF	VS-10CTQ150-N3	UNITS			
Maximum DC reverse voltage	V <sub>R</sub>	150	150	V			
Maximum working peak reverse voltage	V <sub>RWM</sub>	150	150	v			

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST COND	VALUES	UNITS				
Maximum average per leg		50 % duty cycle at $T_{e} = 155$ %	5	А				
See fig. 5 per device	I <sub>F(AV)</sub>		0 % duty cycle at $T_{C}$ = 155 °C, rectangular waveform					
Maximum peak one cycle non-repetitive surge current per leg		5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	620	А			
See fig. 7	ent per leg I <sub>FSM</sub> Condition and with V <sub>RRM</sub> applied			115	~			
Non-repetitive avalanche energy per leg $E_{AS}$ $T_J = 25 \text{ °C}, I_{AS} = 0.30 \text{ A}, L = 150 \text{ mH}$		i0 mH	6.75	mJ				
Repetitive avalanche current per leg		Current decaying linearly to ze Frequency limited by T <sub>J</sub> maxim		0.30	А			

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### **ELECTRICAL SPECIFICATIONS**

PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
		5 A	T <sub>.1</sub> = 25 °C	0.93	
Maximum forward voltage drop per leg	V <sub>FM</sub> <sup>(1)</sup>	10 A	1j=25 C	1.10	V
See fig. 1	VFM ("	5 A	T, = 125 °C	0.73	v
		10 A	1j = 125 C	0.86	
Maximum reverse leakage current per leg	I <sub>RM</sub> <sup>(1)</sup>	T <sub>J</sub> = 25 °C	$V_{\rm B}$ = Rated $V_{\rm B}$	0.05	mA
See fig. 2		T <sub>J</sub> = 125 °C	$v_{\rm R} = Raled v_{\rm R}$	7	
Threshold voltage	V <sub>F(TO)</sub>			0.468	V
Forward slope resistance	r <sub>t</sub>	$T_J = T_J maximum$		28	mΩ
Maximum junction capacitance per leg	CT	$V_{R} = 5 V_{DC}$ (test signal ran	ge 100 kHz to 1 MHz) 25 °C	200	pF
Typical series inductance per leg	L <sub>S</sub>	Measured lead to lead 5 m	8.0	nH	
Maximum voltage rate of change	dV/dt	Rated V <sub>R</sub>	10 000	V/µs	

#### Note

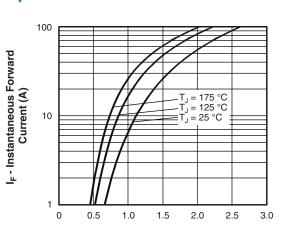
 $^{(1)}\,$  Pulse width < 300  $\mu s,$  duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	)	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 175	°C		
Maximum thermal resistance, junction to case per leg	,		DC operation	3.50			
Maximum thermal resistance, junction to case per package		R <sub>thJC</sub> DC operation	1.75	°C/W			
Typical thermal resistance, case to heatsink (only for TO-220)		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.50			
Approvimate weight				2	g		
Approximate weight				0.07	oz.		
Mounting torque	minimum			6 (5)	kgf ⋅ cm		
Mounting torque	maximum			12 (10)	(lbf $\cdot$ in)		
Marking device			Case style TO-220AB		Q150		



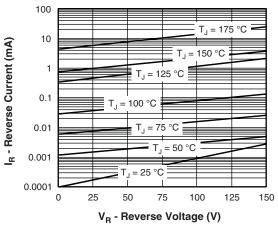
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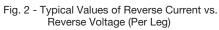
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V<sub>FM</sub> - Forward Voltage Drop (V)

Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)





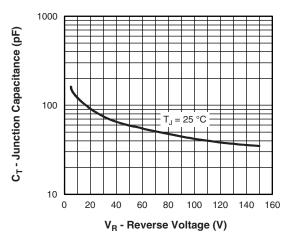
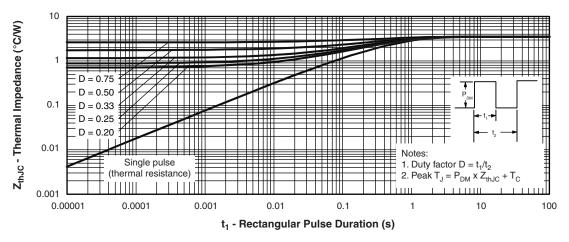
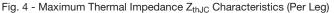


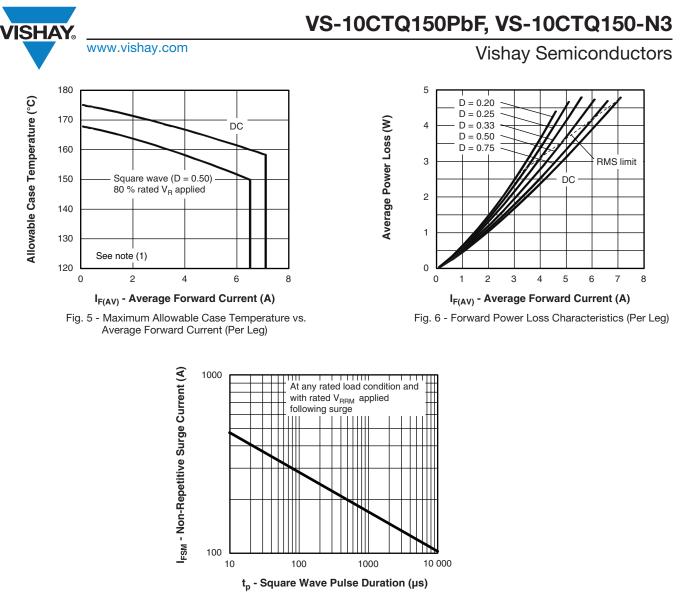
Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)



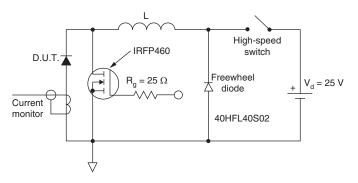


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#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} Pd = Forward power loss = I_{F(AV)} \times V_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 6);} \\ Pd_{REV} = Inverse power loss = V_{R1} \times I_{R} \mbox{ (1 - D); } I_{R} \mbox{ at } V_{R1} = 10 \ V \end{array}$ 

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# VS-10CTQ150PbF, VS-10CTQ150-N3



### Vishay Semiconductors

### **ORDERING INFORMATION TABLE**

Device code	VS-	10	с	т	Q	150	PbF
		2	3	4	5	6	7
	1 2 3	- Cur	rent rati	niconduo ng (10 = iguration	= 10 A)	oduct	
	4	- Pao	Comm kage TO-220	on catho	ode		
	5 6	- Scł - Vol	nottky "C tage rati	)" series ing (150 ntal digil	= 150 \	/)	
		• F	PbF = Le	ead (Pb) alogen-fi	-free ar		

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-10CTQ150PbF	50	1000	Antistatic plastic tube				
VS-10CTQ150-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
Port marking information	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -N3	www.vishay.com/doc?95028			



**Vishay Semiconductors** 

3 x b

3 x b2

Detail B

(b, b2)

b1. b3 Section C - C and D - D

L1 (2)

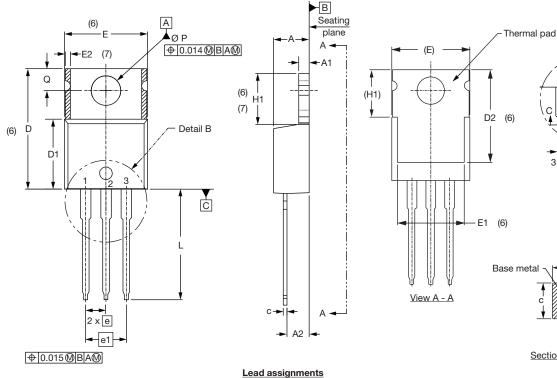
- Plating

c1 (4)

(4)

**TO-220AB** 

### **DIMENSIONS** in millimeters and inches



Lead tip

- **Diodes**
- 1. Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIM	MILLIMETERS INCHES			NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- <sup>(2)</sup> Lead dimension and finish uncontrolled in L1
- <sup>(3)</sup> Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed  $0.127 \text{ mm} (0.005^{\circ})$  per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left( 4\right) }$  Dimension b1, b3 and c1 apply to base metal only
- <sup>(5)</sup> Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° t	o 93°	

(7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed

Outline conforms to JEDEC TO-220, except A2 (maximum) and (8) D2 (minimum) where dimensions are derived from the actual package outline

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